



SPC6604

N & P Pair Enhancement Mode MOSFET

DESCRIPTION

The SPC6604 is the N- and P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

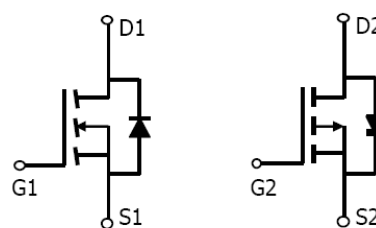
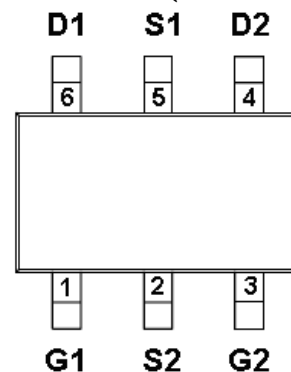
FEATURES

- ◆ N-Channel
20V/4.0A, $R_{DS(ON)}=50m\Omega@V_{GS}=4.5V$
20V/3.4A, $R_{DS(ON)}=60m\Omega@V_{GS}=2.5V$
20V/2.8A, $R_{DS(ON)}=75m\Omega@V_{GS}=1.8V$
- ◆ P-Channel
-20V/-3.4A, $R_{DS(ON)}=85m\Omega@V_{GS}=-4.5V$
-20V/-2.4A, $R_{DS(ON)}=110m\Omega@V_{GS}=-2.5V$
-20V/-1.7A, $R_{DS(ON)}=130m\Omega@V_{GS}=-1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TSOT-23- 6P package design

APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

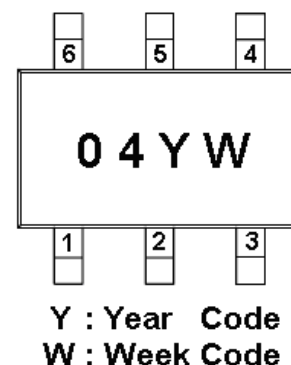
PIN CONFIGURATION(TSOT-23- 6P)



n-channel

p-channel

PART MARKING





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PIN DESCRIPTION

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPC6604TS26RGB	TSOT-23- 6P	04YW

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)

※ SPC6604TS26RGB : Tape Reel ; Pb – Free ; Halogen -Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter		Symbol	Typical		Unit
			N-Channel	P-Channel	
Drain-Source Voltage		V _{DSS}	20	-20	V
Gate –Source Voltage		V _{GSS}	±12	±12	V
Continuous Drain Current(T _J =150℃)	T _A =25℃	4.0	-3.4	-2.8	A
	T _A =70℃	3.4	-2.4	-2.1	
Pulsed Drain Current		I _{DM}	10	-8	A
Continuous Source Current(Diode Conduction)		I _S	1.6	-1.4	A
Power Dissipation	T _A =25℃	P _D	1.15		W
	T _A =70℃		0.75		
Operating Junction Temperature		T _J	-55/150		℃
Storage Temperature Range		T _{STG}	-55/150		℃
Thermal Resistance-Junction to Ambient	T ≤ 10sec	R _{θJA}	50	52	℃/W
	Steady State		90	90	



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ELECTRICAL CHARACTERISTICS

(T_A=25°C Unless otherwise noted)

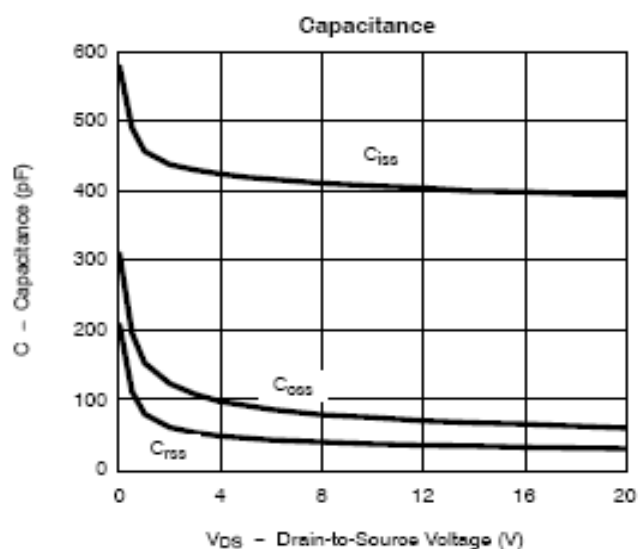
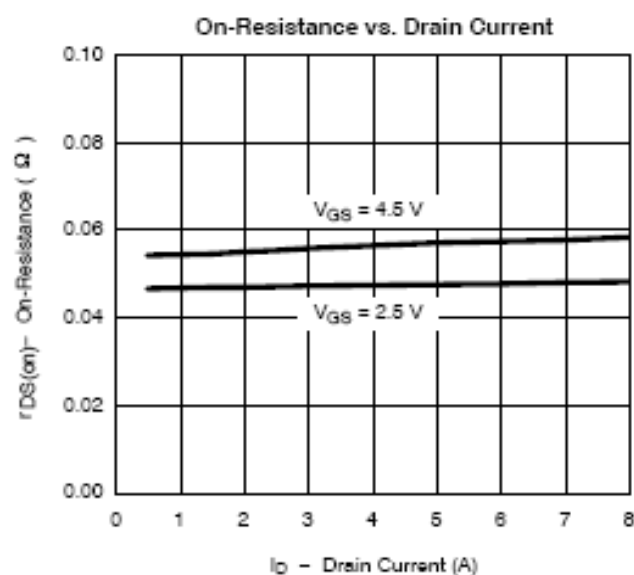
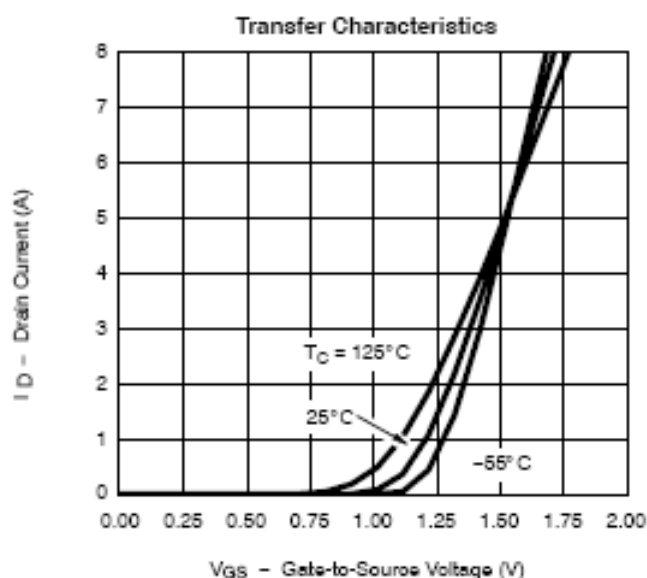
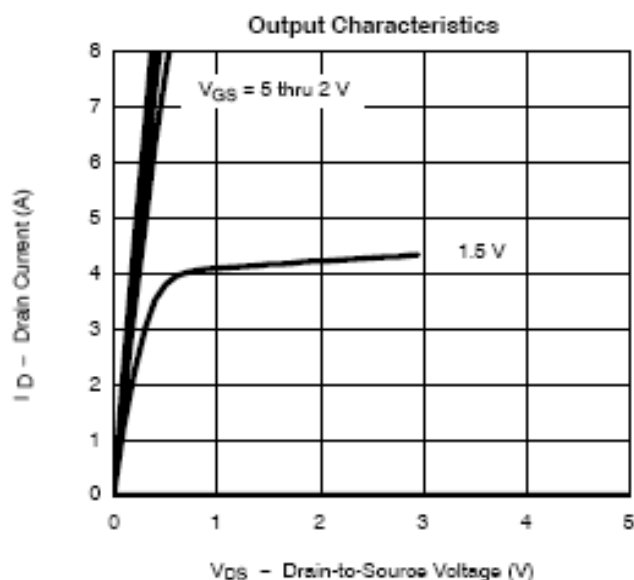
Parameter	Symbol	Conditions		Min.	Typ	Max.	Unit
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V,I _D = 250uA	N-Ch	20			V
		V _{GS} =0V,I _D =-250uA	P-Ch	-20			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250uA	N-Ch	0.4		1.0	
		V _{DS} =V _{GS} ,I _D =-250uA	P-Ch	-0.35		-0.8	
Gate Leakage Current	I _{GSS}	V _{DS} =0V,V _{GS} =±12V	N-Ch			±100	nA
		V _{DS} =0V,V _{GS} =±12V	P-Ch			±100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16V,V _{GS} =0V	N-Ch			1	uA
		V _{DS} =-16V,V _{GS} =0V	P-Ch			-1	
		V _{DS} = 16V,V _{GS} =0V T _J =55℃	N-Ch			10	
		V _{DS} =-16V,V _{GS} =0V T _J =55℃	P-Ch			-10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 4.5V,V _{GS} = 10V	N-Ch	6			A
		V _{DS} ≤ -4.5V,V _{GS} =-10V	P-Ch	-6			
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V,I _D =4.0A	N-Ch		0.040	0.050	Ω
		V _{GS} =-4.5V,I _D =-3.4A	P-Ch		0.068	0.085	
		V _{GS} =2.5V,I _D =3.4A	N-Ch		0.046	0.060	
		V _{GS} =-2.5V,I _D =-2.4A	P-Ch		0.090	0.110	
		V _{GS} =1.8V,I _D =2.8A	N-Ch		0.056	0.075	
		V _{GS} =-1.8V,I _D =-1.7A	P-Ch		0.113	0.130	
Forward Transconductance	g _{fs}	V _{DS} =5V,I _D =-3.6A	N-Ch		10		S
		V _{DS} =-5V,I _D =-2.8A	P-Ch		6		
Diode Forward Voltage	V _{SD}	I _S =1.6A,V _{GS} =0V	N-Ch		0.8	1.2	V
		I _S =-1.5A,V _{GS} =0V	P-Ch		-0.8	-1.2	
Dynamic							
Total Gate Charge	Q _g	N-Channel V _{DS} =6V,V _{GS} =4.5V, I _D ≡2.8A P-Channel V _{DS} =-6V,V _{GS} =-4.5V ,I _D ≡-2.8A	N-Ch		4.8	8	nC
Gate-Source Charge	Q _{gs}		P-Ch		4.8	8	
			N-Ch		1.0		
Gate-Drain Charge	Q _{gd}		P-Ch		1.0		
			N-Ch		1.0		
Turn-On Time	td(on)		N-Channel V _{DD} =6V,R _L =6Ω ,I _D ≡1.0A V _{GEN} =4.5V ,R _G =6Ω P-Channel V _{DD} =-6V,R _L =6Ω ,I _D ≡-1.0A V _{GEN} =-4.5V ,R _G =6Ω	N-Ch		8	
	P-Ch			10	16		
	N-Ch			12	18		
	P-Ch			13	23		
Turn-Off Time	td(off)	N-Ch			30	35	
	tf	P-Ch			18	25	
		N-Ch			12	16	
				P-Ch		15	20



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TYPICAL CHARACTERISTICS (N-Channel)

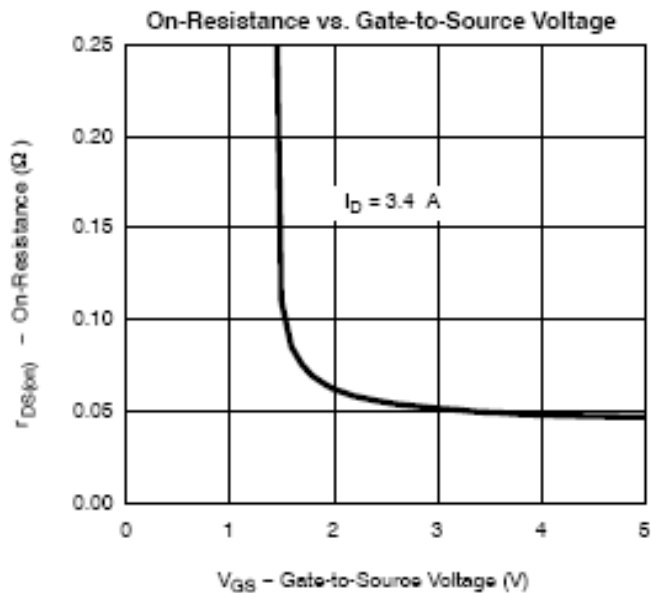
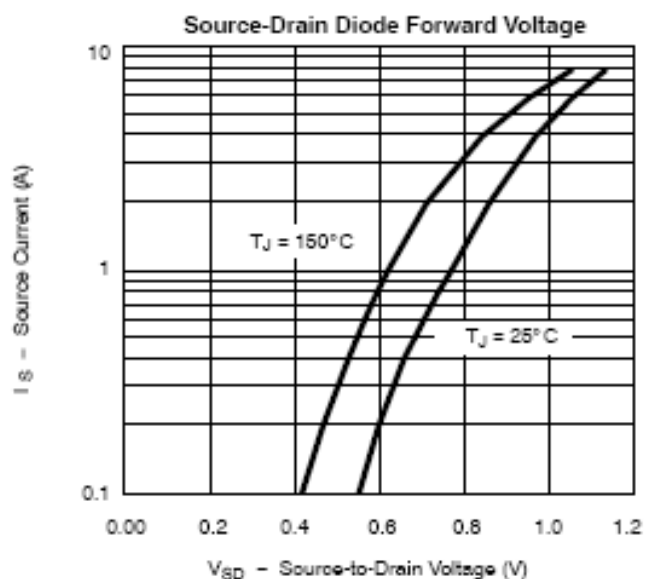
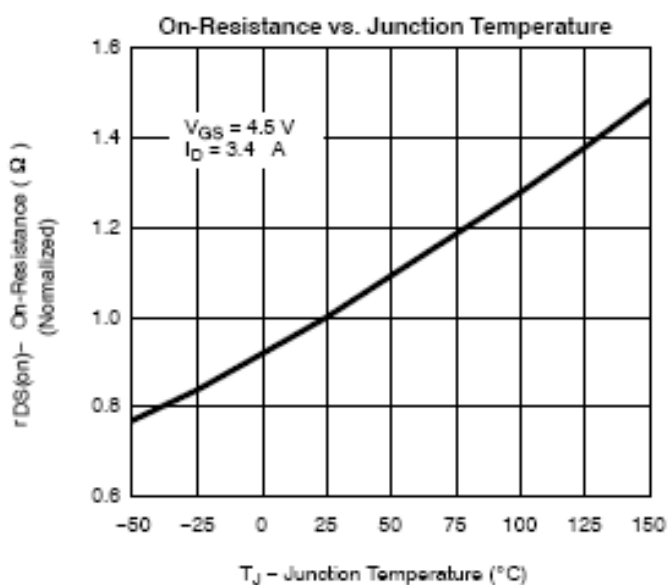
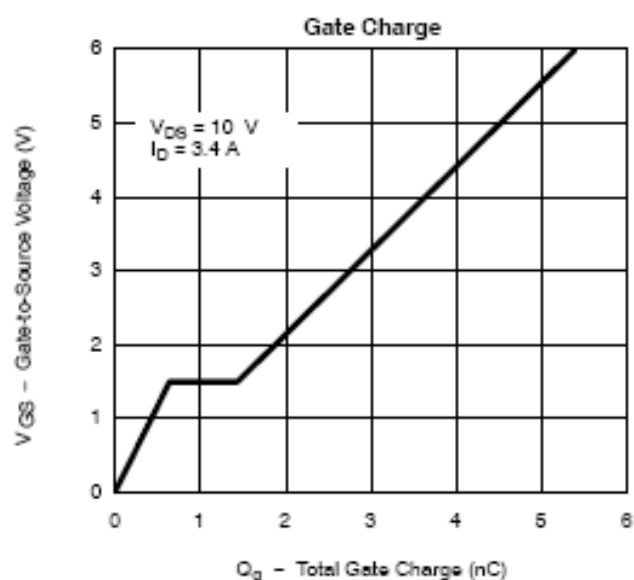




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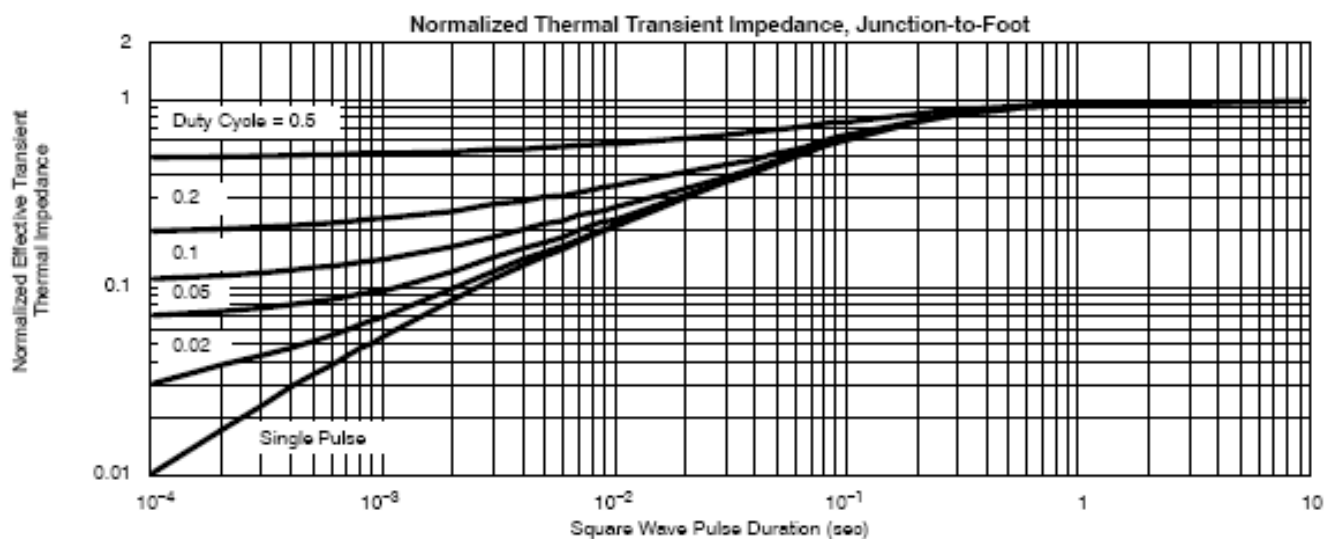
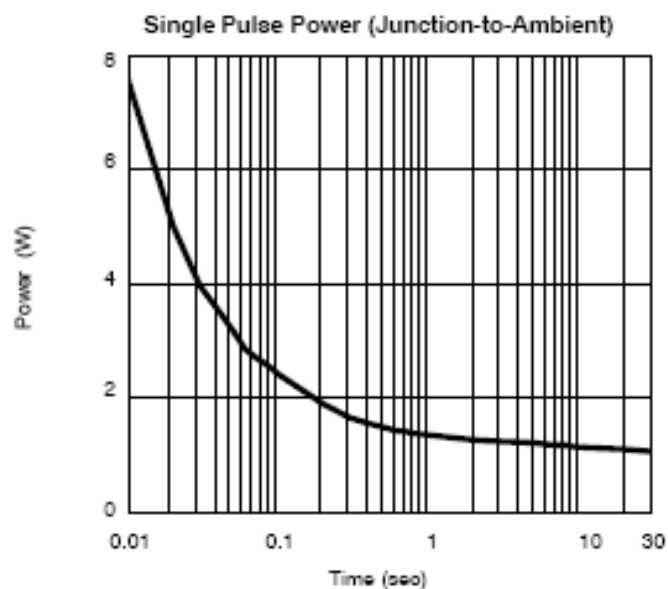
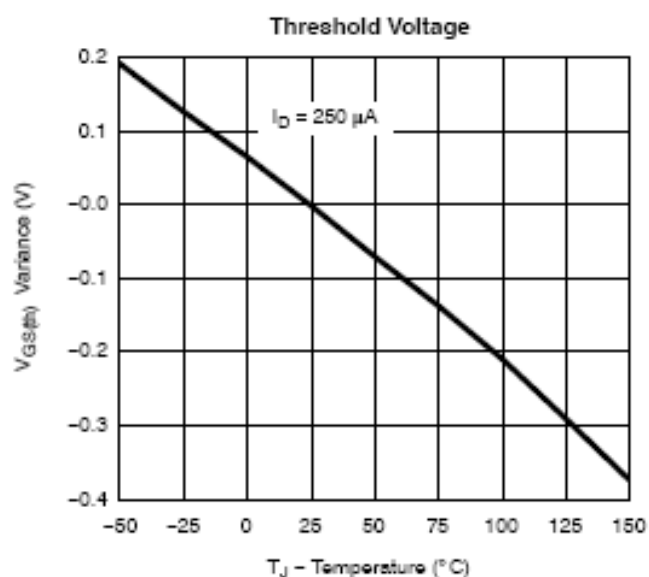




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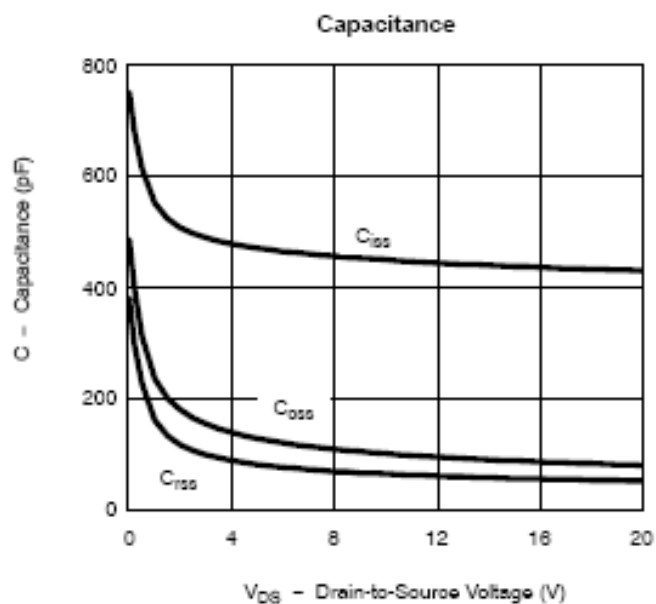
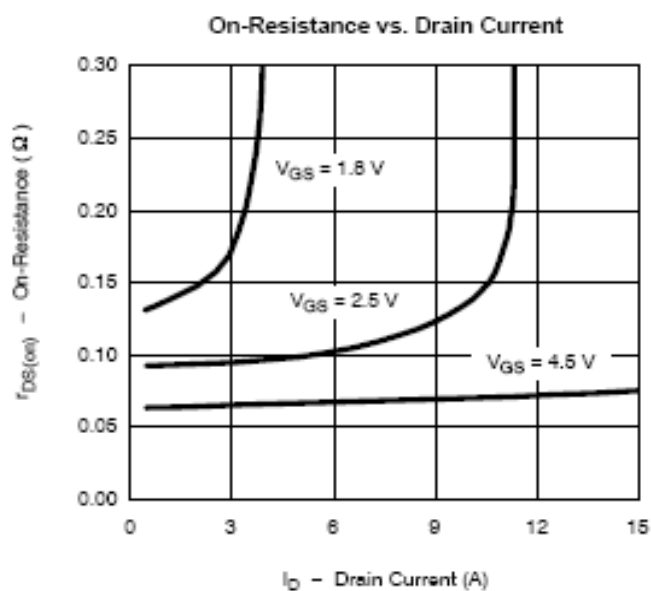
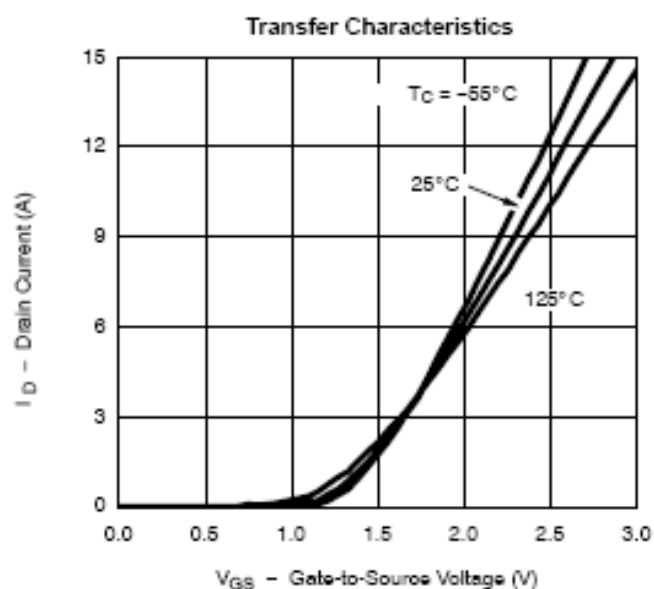
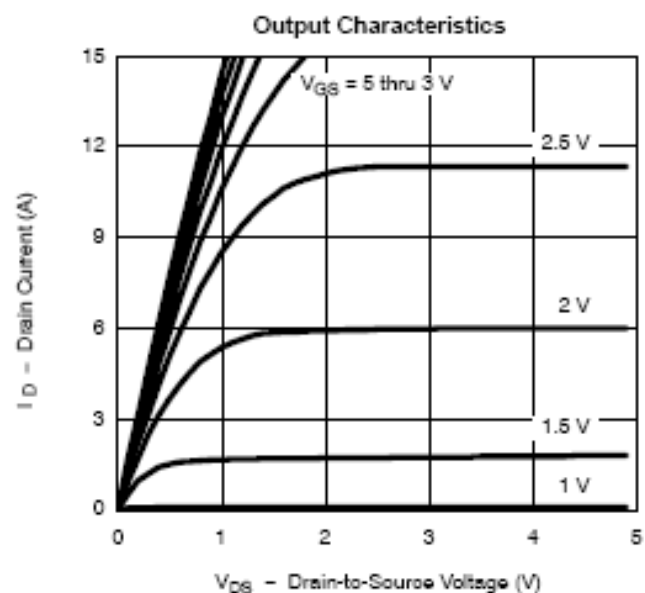




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TYPICAL CHARACTERISTICS (P-Channel)

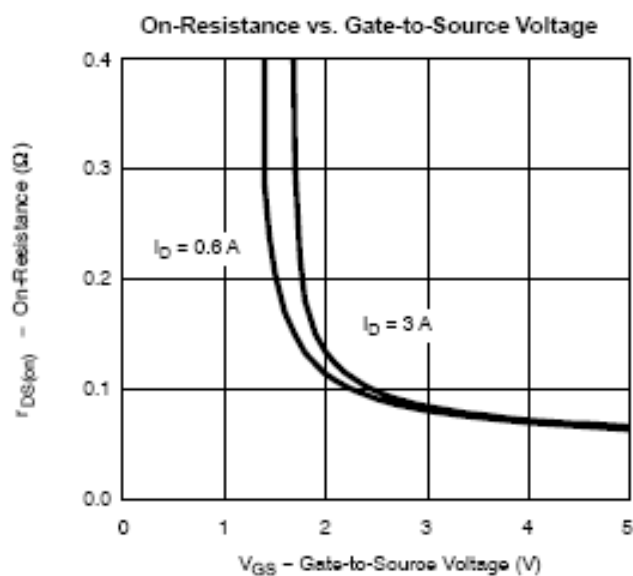
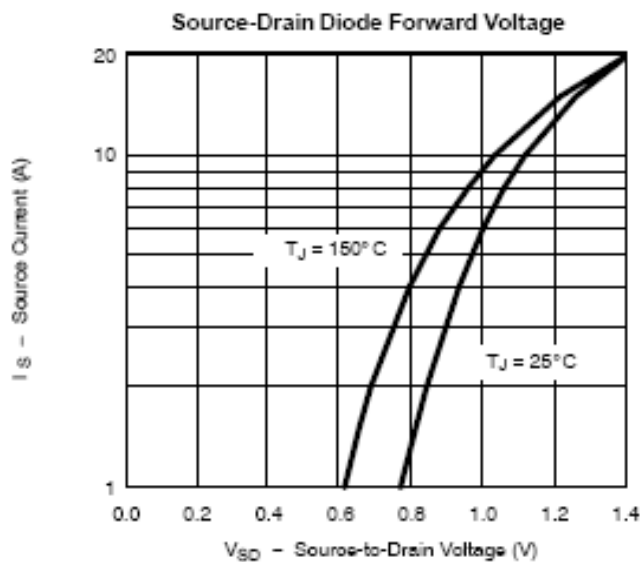
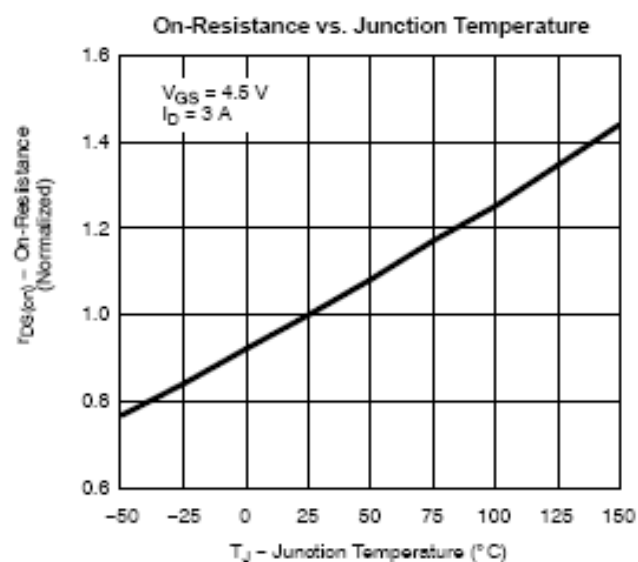
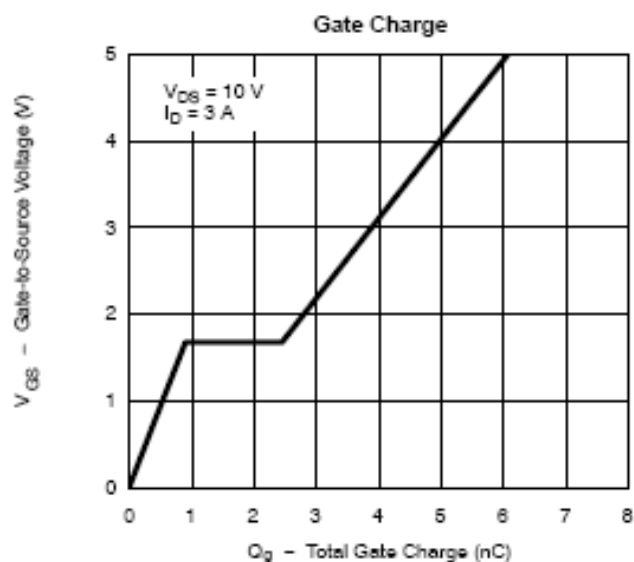




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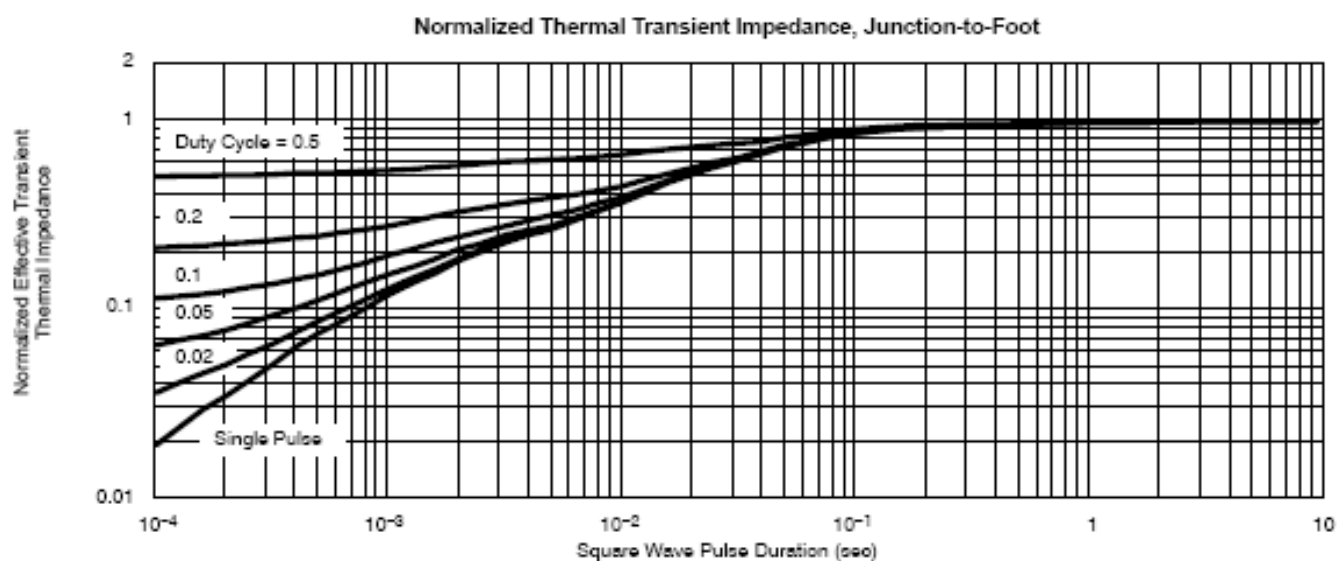
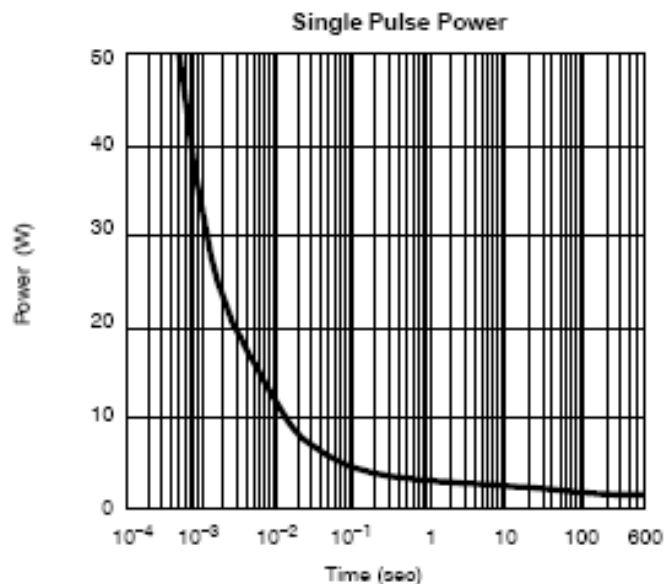
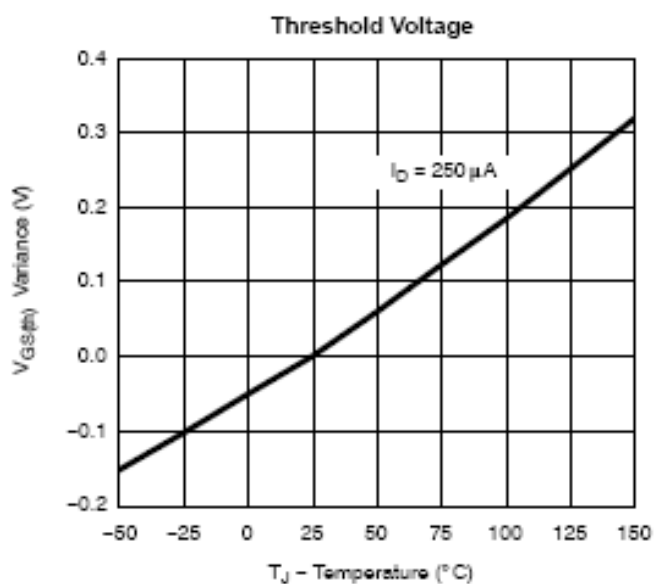




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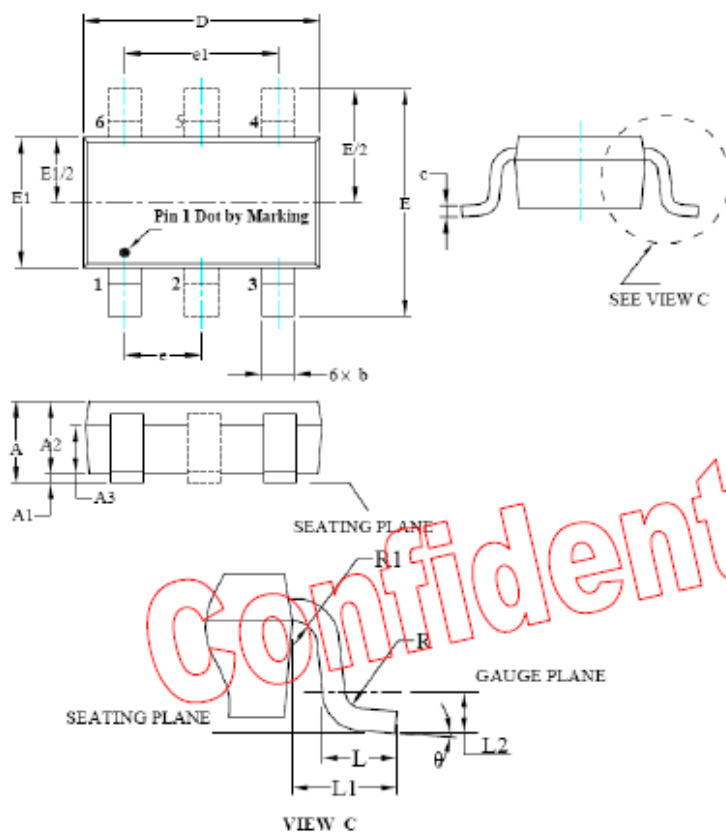




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TSOP- 6P PACKAGE OUTLINE



SYMBOL	VARIATION					
	TSOT-2X					
	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	0.700	0.860	1.000	0.028	0.034	0.040
A1	0.000	0.060	0.100	0.000	0.002	0.004
A2	0.700	0.800	0.900	0.028	0.031	0.035
A3	—	0.420	0.520	—	0.017	0.020
b	0.300	0.425	0.500	0.012	0.017	0.020
c	0.080	0.138	0.200	0.003	0.005	0.008
D	2.692	2.900	3.099	0.106	0.114	0.122
E	2.591	2.800	3.000	0.102	0.110	0.118
E1	1.397	1.600	1.803	0.055	0.063	0.071
e	0.950 BSC			0.037 BSC		
e1	1.900 BSC			0.075 BSC		
L	0.300	0.450	0.600	0.012	0.018	0.024
L1	0.600 REF			0.024 REF		
L2	0.250 BSC			0.010 BSC		
R	0.100	—	—	0.004	—	—
R1	0.100	—	0.250	0.004	—	0.010
θ	0°	—	6°	0°	—	6°



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